

## 650V N-Channel Silicon Carbide Power MOSFET

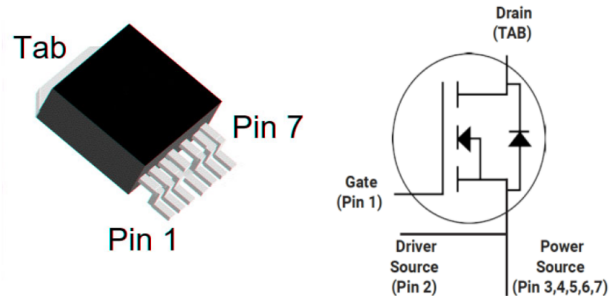
### Features:

- High blocking voltage with low  $R_{DS(ON)}$
- Fast switching speed with low capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

### Applications:

- Switch Mode Power Supplies
- Battery charges
- High voltage DC/DC converters
- Motor Drives
- Solar inverters

### Package:



Part Number	Package
DTK30N65SC7	TO-263-7L

### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
$V_{DS}$	Drain-Source voltage	650	V	$V_{GS}=0\text{V}$ , $I_D=100\mu\text{A}$
$V_{GS}$	Gate-Source voltage	-5 to 20	V	static
$V_{GS}$	Gate-Source voltage	-10 to 25	V	dynamic
$I_D$	Drain current (continuous)	30	A	$T_c=25^\circ\text{C}$
		22	A	$T_c=100^\circ\text{C}$
$I_{DM}$	Drain current (pulsed)	65	A	
$P_{TOT}$	Total power dissipation	171	W	$T_c=25^\circ\text{C}$
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$	
$T_J$	Operating junction temperature	-55 to 150	$^\circ\text{C}$	

### Thermal Data

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Thermal Resistance from Junction to Case	0.73	$^\circ\text{C/W}$
$R_{\theta(J-A)}$	Thermal Resistance from Junction to Case	35	$^\circ\text{C/W}$

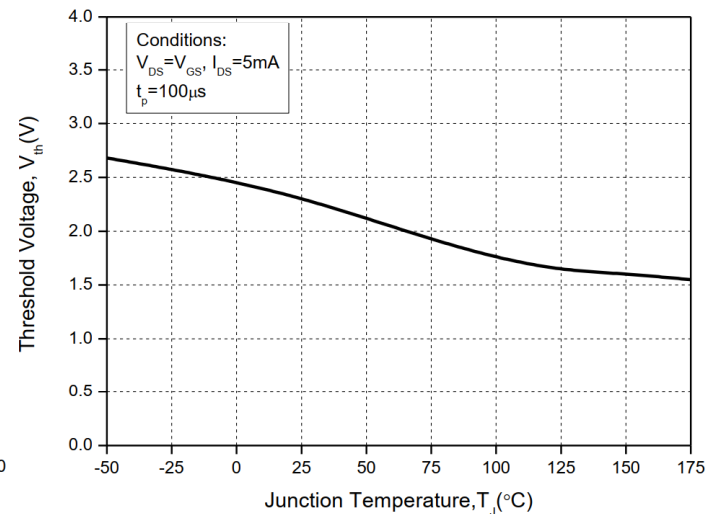
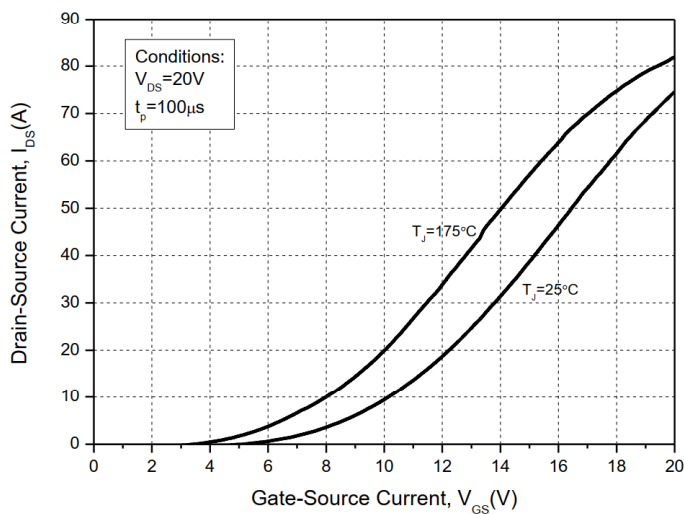
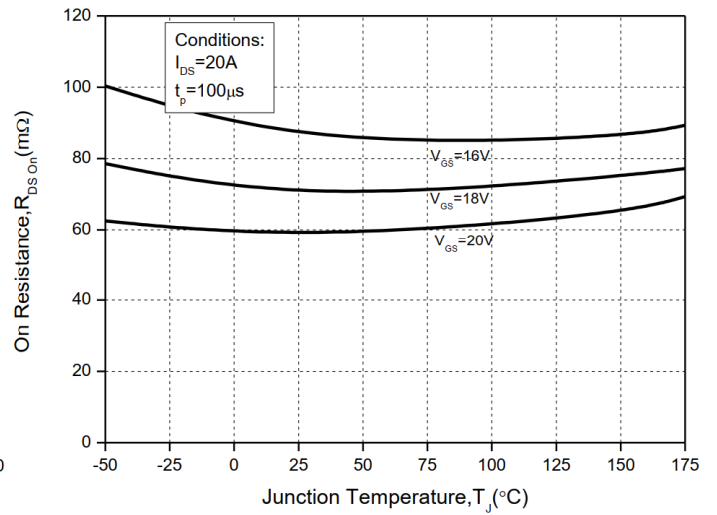
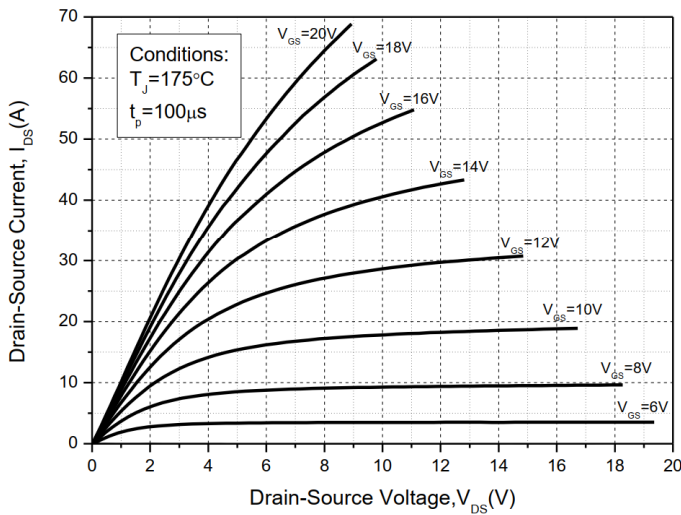
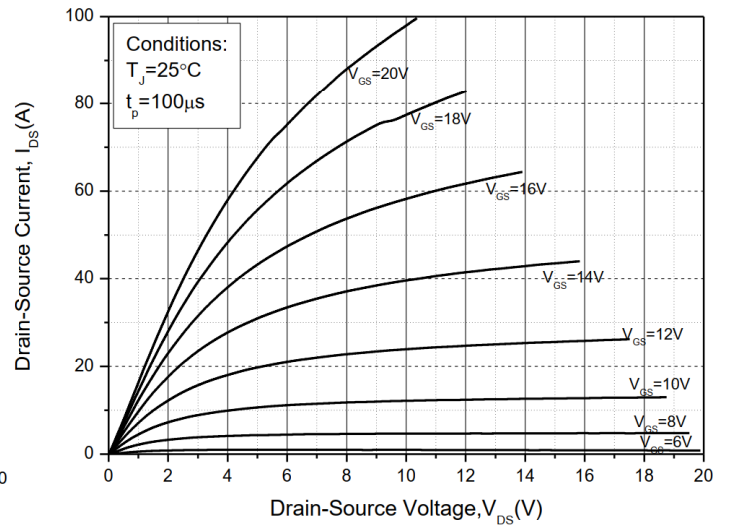
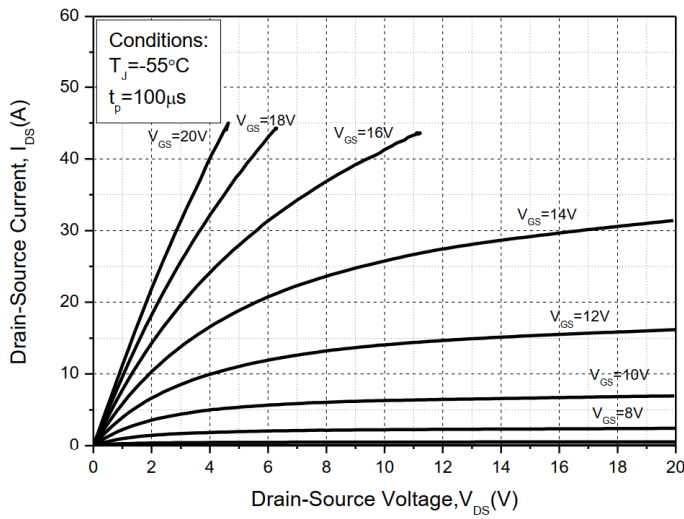
**Electrical Characteristics** ( $T_c=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
$I_{DSS}$	Zero gate voltage drain current		2	100	$\mu\text{A}$	$V_{DS}=650\text{V}, V_{GS}=0\text{V}$
$I_{GSS}$	Gate leakage current		50	$\pm 200$	nA	$V_{DS}=0\text{V}, V_{GS}=20\text{V}$
$V_{TH}$	Gate threshold voltage		2.4	4	V	$V_{GS}=V_{DS}, I_D=5\text{mA}$
			1.8		V	$V_{GS}=V_{DS}, I_D=5\text{mA}$ @ $T_c=150^\circ\text{C}$
$R_{ON}$	Static drain-source on-resistance		60	80	m $\Omega$	$V_{GS}=20\text{V}, I_D=20\text{A}$ @ $T_c=25^\circ\text{C}$
			95		m $\Omega$	$V_{GS}=20\text{V}, I_D=20\text{A}$ @ $T_c=175^\circ\text{C}$
$C_{iss}$	Input capacitance		1700		pF	$V_{DS}=1000\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}, V_{AC}=25\text{mV}$
$C_{oss}$	Output capacitance		172		pF	
$C_{rss}$	Reverse transfer capacitance		77		pF	
$E_{oss}$	$C_{oss}$ stored energy		20		$\mu\text{J}$	
$Q_g$	Total gate charge		65		nC	$V_{DS}=400\text{V}, I_D=10\text{A},$ $V_{GS}=0$ to $20\text{V}$
$Q_{gs}$	Gate-source charge		18		nC	
$Q_{gd}$	Gate-drain charge		19		nC	
$R_g$	Gate input resistance		2.0		$\Omega$	$f=1\text{MHz}, V_{AC}=25\text{mV}$
$G_{FS}$	Forward Transconductance		4.7		S	$V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}$
			5.9		S	$V_{DS} = 20 \text{ V}, I_D = 20 \text{ A},$ $T_J = 175^\circ\text{C}$

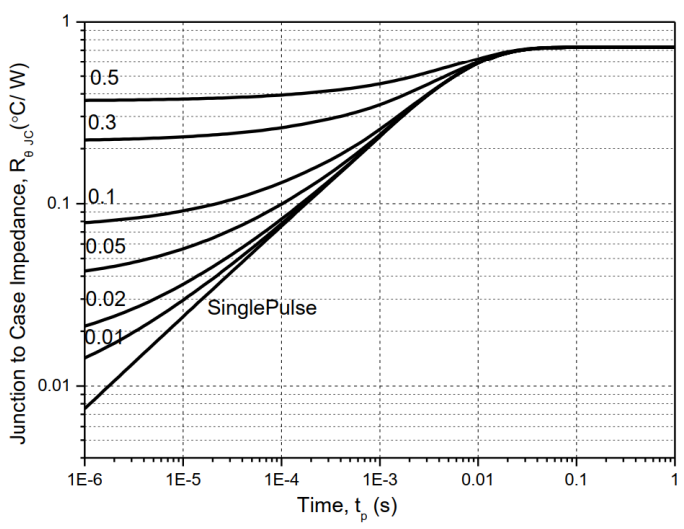
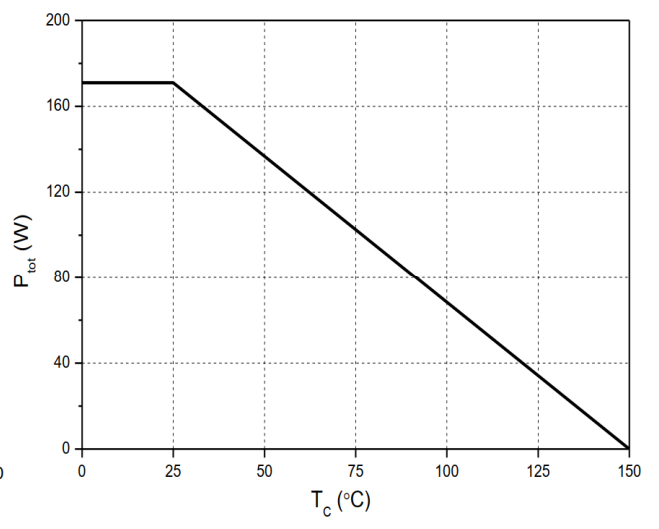
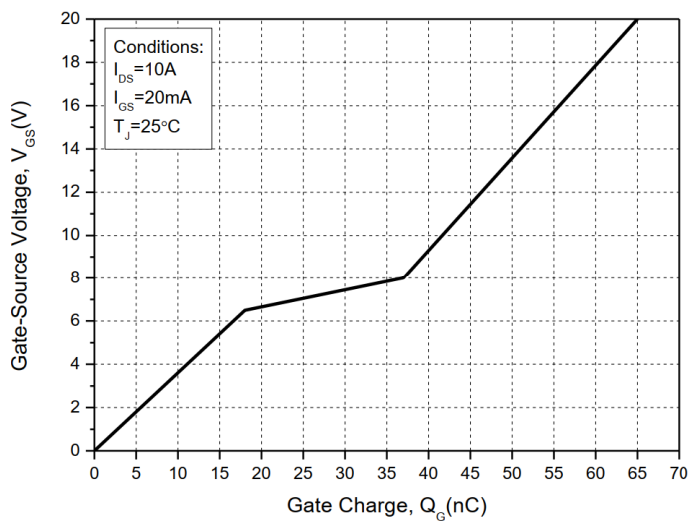
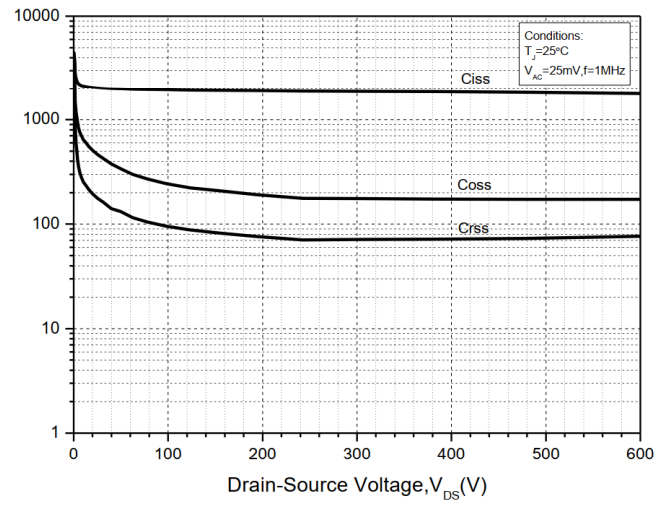
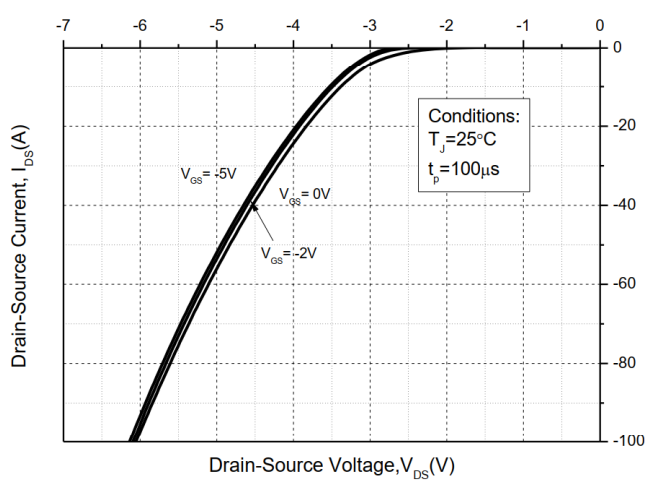
**Reverse Diode Characteristics** ( $T_c=25^\circ\text{C}$  unless otherwise specified)

<b>Switching Characteristics</b>							
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units	
$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = 400\text{ V}$ , $I_D = 10\text{ A}$ , $V_{GS} = -0/+20\text{ V}$ , $R_{G,EXT} = 5\ \Omega$ $R_L = 40\ \Omega$ , Timing relative to $V_{DS}$		15		ns	
$T_R$	Rise Time			45		ns	
$T_{D(OFF)}$	Turn Off Delay Time				13		ns
$T_F$	Fall Time				10		ns
$E_{ON}$	Turn On Energy	$V_{DD} = 400\text{ V}$ , $I_D = 10\text{ A}$ , $V_{GS} = -0/+20\text{ V}$ , $R_{G,EXT} = 5\ \Omega$ $L = 142\ \mu\text{H}$		140		$\mu\text{J}$	
$E_{OFF}$	Turn Off Energy				32		$\mu\text{J}$
<b>Drain-Source Diode Characteristics</b> ( $T_J = 25^\circ\text{C}$ unless otherwise noted)							
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				30	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current				65	A	
$V_{SD}$	Diode Forward Voltage	$V_{GS} = -5\text{ V}$ , $I_{SD} = 10\text{ A}$		3.5		V	
		$V_{GS} = -5\text{ V}$ , $I_{SD} = 10\text{ A}$ , $T_J = 175^\circ\text{C}$		3.3		V	
$I_{RM}$	Peak Reverse Recovery Current	$V_{GS} = -5\text{ V}$ , $I_{SD} = 20\text{ A}$ , $V_R = 400\text{ V}$ , $di/dt = 1000\text{ A}/\mu\text{S}$		12		A	
$T_{RR}$	Reverse Recovery Time			37		ns	
$Q_{RR}$	Reverse Recovery Charge				198		nC

Typical Performance (curves)



Typical Performance (curves)



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